

Customer No.: 31561  
Application No.: 10/605,403  
Docket No.: 11401-US-PA

In The Claims:

**Claim 1. (currently amended) A method for fabricating a thin film transistor (TFT), comprising:**

**forming a gate on a substrate, the gate comprising a MoNb alloy composite layer of MoNb/AlNd or MoNb/AlNd/MoNb;**

**forming an insulating layer over the substrate covering the gate;**

**forming a channel layer on the insulating layer above the gate; and**

**forming a source/drain on the channel layer.**

**Claim 2. (original) The method of claim 1, wherein an amount of niobium in the MoNb alloy is less than 10%.**

**Claims 3-4. (canceled)**

**Claim 5. (original) The method of claim 1, wherein the source/drain comprises a single MoNb layer or a composite layer of MoNb/AlNd or MoNb/AlNd/MoNb.**

**Claim 6. (original) The method of claim 5, wherein an amount of niobium in the MoNb alloy is less than 10%.**

**Claim 7. (currently amended) A method for fabricating a thin film transistor (TFT), comprising:**

**forming a gate on a substrate;**

**forming an insulating layer over the substrate covering the gate;**

**forming a channel layer on the insulating layer above the gate; and**

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**forming a source/drain on the channel layer, the source/drain comprising a MoNb alloy composite layer of MoNb/AlNd or MoNb/AlNd/MoNb.**

**Claim 8. (original) The method of claim 7, wherein an amount of niobium in the MoNb alloy is less than 10%.**

**Claims 9-10. (canceled)**

**Claim 11. (currently amended) A thin film transistor (TFT), comprising:**  
**a gate on a substrate, the gate comprising a MoNb alloy composite layer of MoNb/AlNd or MoNb/AlNd/MoNb;**  
**an insulating layer over the substrate covering the gate;**  
**a channel layer on the insulating layer above the gate; and**  
**a source/drain on the channel layer.**

**Claim 12. (original) The TFT of claim 11, wherein an amount of niobium in the MoNb alloy is less than 10%.**

**Claims 13-14. (canceled)**

**Claim 15. (original) The TFT of claim 11, wherein the source/drain comprises a single MoNb layer or a composite layer of MoNb/AlNd or MoNb/AlNd/MoNb.**

**Claim 16. (original) The TFT of claim 15, wherein an amount of niobium in the MoNb alloy is less than 10%.**

**Claim 17. (previously presented) A thin film transistor (TFT), comprising:**

**a gate on a substrate;**

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**an insulating layer over the substrate covering the gate;**  
**a channel layer on the insulating layer above the gate; and**  
**a source/drain on the channel layer, the source/drain comprising a composite layer**  
**of MoNb/AlNd or MoNb/AlNd/MoNb.**

**Claim 18. (original) The method of claim 17, wherein an amount of niobium in the**  
**MoNb alloy is less than 10%.**

**Claims 19-20 (canceled)**

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